

30 V, single N-channel Trench MOSFET Rev. 1 — 8 May 2012

Product data sheet

1. **Product profile**

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- Low threshold voltage

1.3 Applications

- Relay driver
- High-speed line driver

1.4 Quick reference data

- Ultra thin package profile with 0.37 mm height
- ESD protection up to 2 kV
- Low-side loadswitch
- Switching circuits

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	900	mA
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C		-	370	490	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source		
3	D	drain	2 Transparent top view SOT883B (DFN1006B-3)	

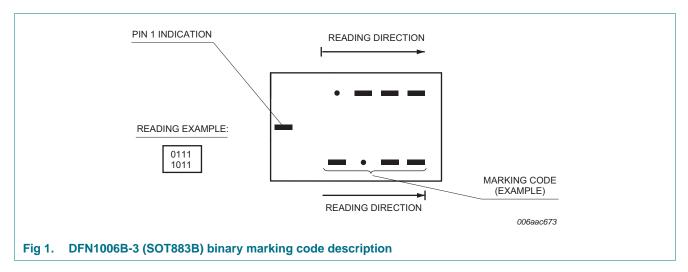
3. Ordering information

Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
PMZB370UNE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB370UNE	0000 1000



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5. Limiting values

Table 5. Limiting values

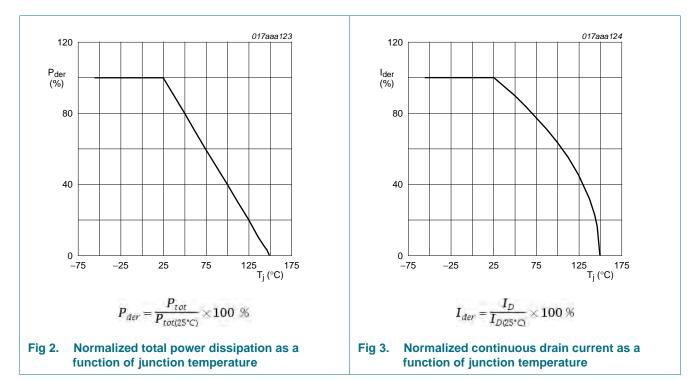
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j = 25 °C		-	30	V
gate-source voltage			-8	8	V
drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	900	mA
	$V_{GS} = 4.5 \text{ V}; \text{ T}_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	560	mA
peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	3.6	А
total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
		[1]	-	715	mW
	T _{sp} = 25 °C		-	2700	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					
source current	T _{amb} = 25 °C	<u>[1]</u>	-	680	mA
n rating					
electrostatic discharge voltage	НВМ	[3]	-	2000	V
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature diode source current n rating	$\label{eq:drain-source voltage} T_j = 25 \ ^{\circ}\text{C}$ $\begin{tabular}{lllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \mbox{drain-source voltage} & $T_j = 25 \ {}^{\circ}\ C $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $	$ \begin{array}{c} \mbox{drain-source voltage} & $T_j = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ $gate-source voltage & $V_{GS} = 4.5 \ V; \ $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 100 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 100 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 100 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ $V_{GS} = 4.5 \ V; \ $T_{amb} = 100 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ \hline $V_{GS} = 4.5 \ V; \ $T_{amb} = 100 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ \hline $V_{GS} = 4.5 \ V; \ $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & 11 & $-$ \\ \hline $total power dissipation & $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ \hline $total power dissipation & $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ \hline $total power dissipation & $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $T_{amb} = 25 \ {}^{\circ}\mbox{C}$ & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $total power dissipation & $-$ \\ \hline $total power dissipation & $total power di$	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

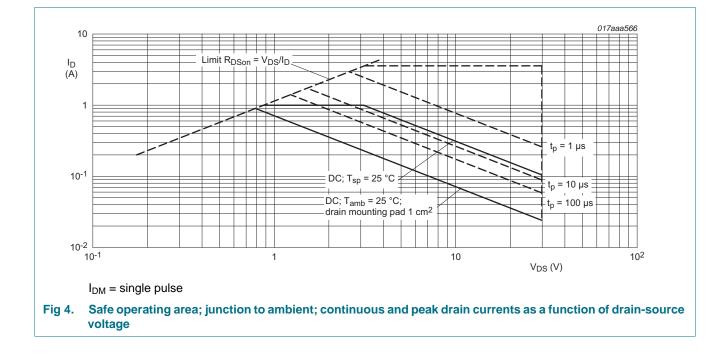
[3] Measured between all pins.



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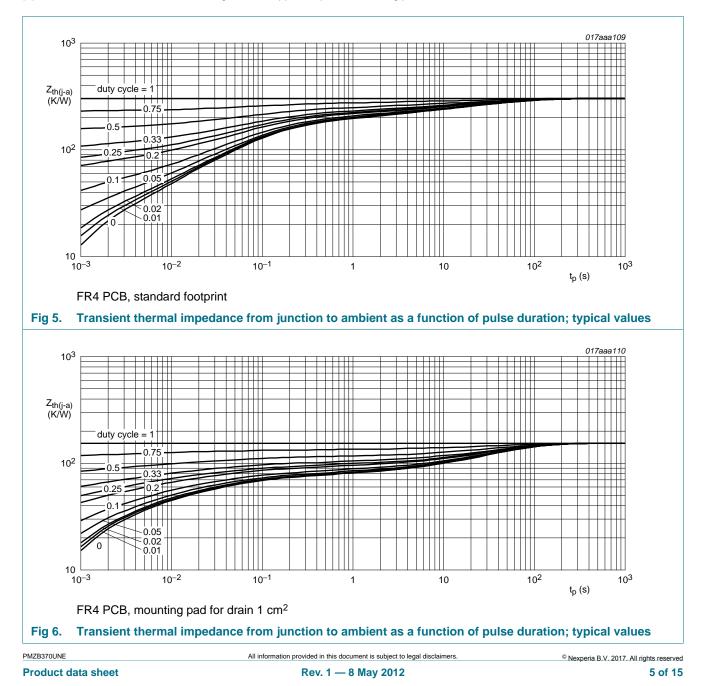
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6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	305	360	K/W
	from junction to ambient		[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



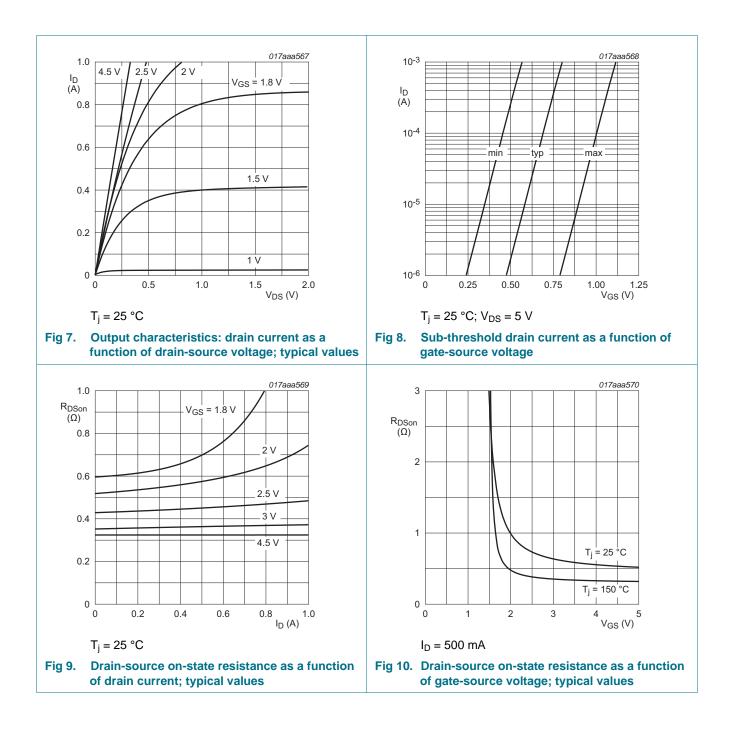
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7. Characteristics

Table 7.	Characteristics	O and dition of		T .		11.24
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.5	0.77	1.05	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; \text{T}_{j} = 25 ^{\circ}\text{C}$	-	-	3	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; \text{T}_{j} = 25 ^{\circ}\text{C}$	-	-	3	μΑ
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μΑ
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C	-	370	490	mΩ
		V_{GS} = 4.5 V; I _D = 500 mA; T _j = 150 °C	-	650	860	mΩ
		V_{GS} = 2.5 V; I_D = 400 mA; T_j = 25 °C	-	470	750	mΩ
		V_{GS} = 1.8 V; I _D = 100 mA; T _j = 25 °C	-	630	1300	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	1580	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I _D = 500 mA; V _{GS} = 4.5 V;	-	0.77	1.16	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q _{GD}	gate-drain charge		-	0.16	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; \text{ f} = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	52	78	pF
C _{oss}	output capacitance	T _j = 25 °C	-	9	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 250 $\Omega;$ V_{GS} = 4.5 V;	-	11	22	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	9	-	ns
t _{d(off)}	turn-off delay time		-	54	108	ns
t _f	fall time		-	27	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 300 mA; V _{GS} = 0 V; T _i = 25 °C	0.48	0.76	1.2	V

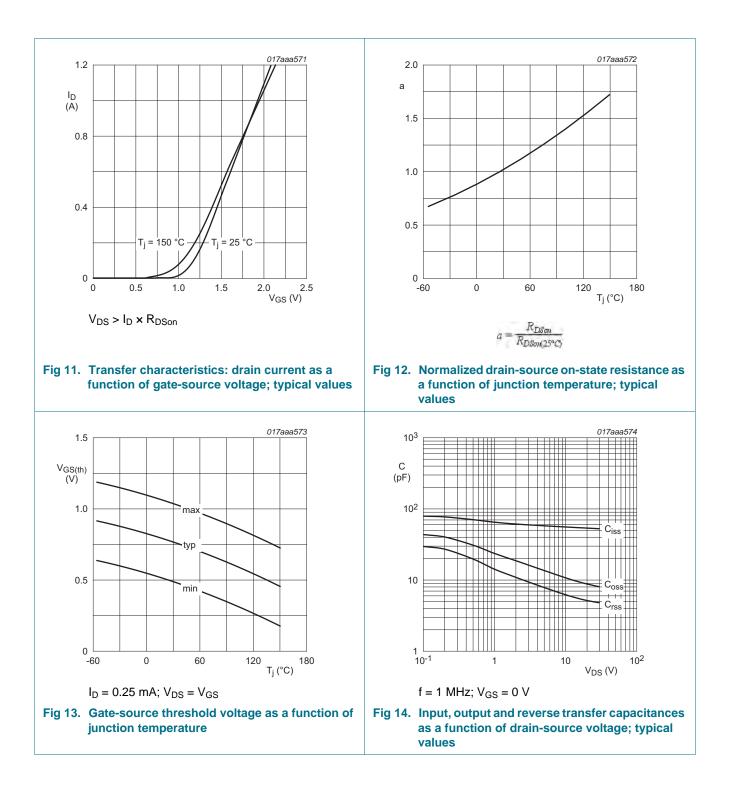
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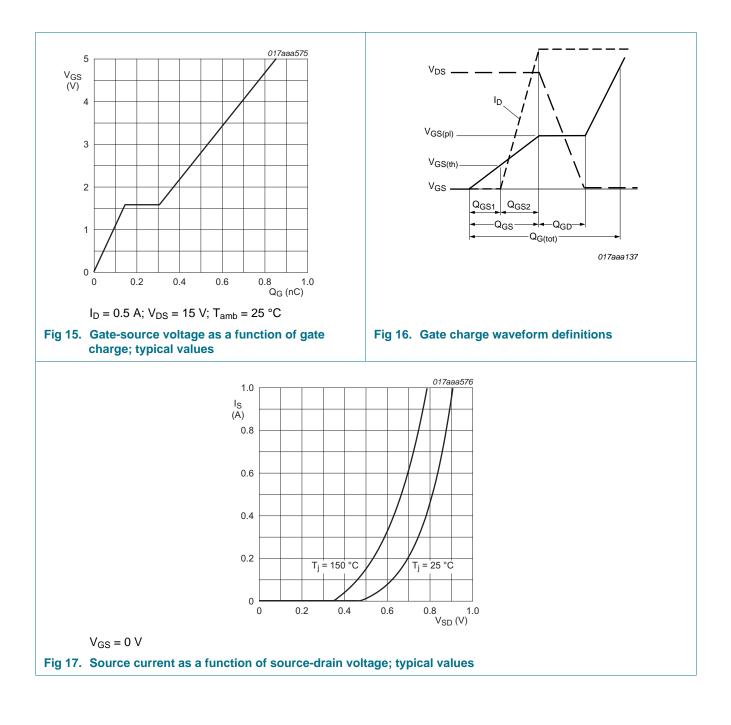
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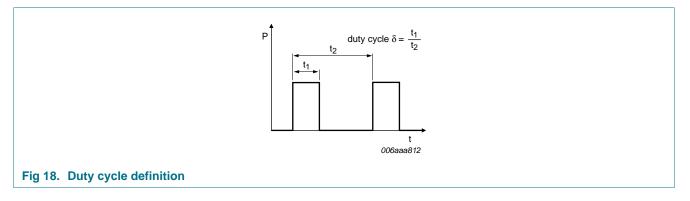
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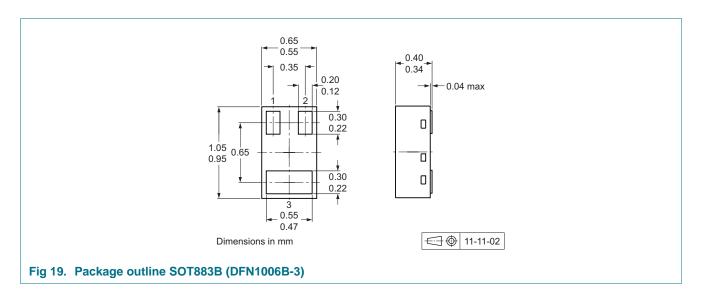


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8. Test information

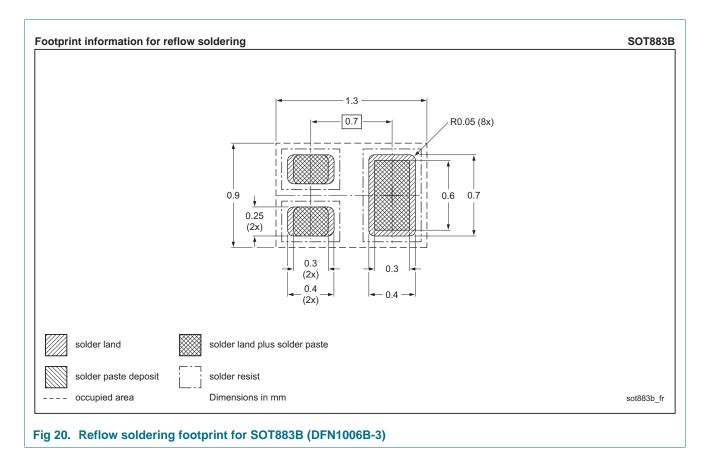


9. Package outline



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10. Soldering



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11. Revision history

Table 8.	Revision history							
Document I	ID	Release date	Data sheet status	Change notice	Supersedes			
PMZB370U	NE v.1	20120508	Product data sheet	-	-			

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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